



60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on) max	ID MAX T _C = +25°C
60V	1.5 m Ω @ V _{GS} = 10 V	225A

Description and Applications

This new generation N-channel enhancement mode MOSFET is designed to minimize $R_{\text{DS}(\text{ON})}$ yet maintain superior switching performance. This device is ideal for use in power management and load switch.

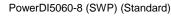
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High-Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- · Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

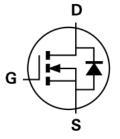
Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

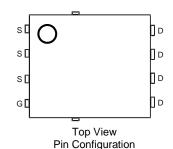








Internal Schematic



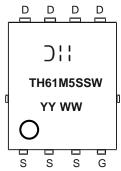
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH61M5SPSW-13	PowerDI5060-8 (SWP) (Standard)	2500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



⊃¦¦ = Manufacturer's Marking TH61M5S<u>\$W</u> = Product Type Marking Code YYWW or YYWW = Date Code Marking YY or YY = Year (ex: 20 = 2020) WW = Week (01 to 53)

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August 2020

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Durin Compant VI 40V/(Nata C)	Tc = +25°C	- I _D	225	- A
Continuous Drain Current, V _{GS} = 10V (Note 6)	T _C = +100°C		160	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	225	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	IDM	900	А	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		Ism	900	Α
Avalanche Current, L = 1mH		I _{AS}	35.8	Α
Avalanche Energy, L = 1mH		Eas	640.8	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	3.2	W
Thermal Resistance, Junction to Ambient (Note 5)		RθJA	47	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	PD	167	W
Thermal Resistance, Junction to Case (Note 6)		R _θ JC	0.9	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	•			,	,		
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	-		1	μΑ	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	Igss	ı		±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	1	1.1	1.5	mΩ	$V_{GS} = 10V, I_D = 30A$	
Diode Forward Voltage	VsD	1	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	8306	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	-	2735	_	pF		
Reverse Transfer Capacitance	C _{rss}	1	184	_			
Gate Resistance	Rg	1	3.0	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	130.6	_		V _{DS} = 30V, I _D = 30A, V _{GS} = 10V	
Gate-Source Charge	Q_{gs}	_	30.4	_	nC		
Gate-Drain Charge	Q _{gd}	_	28.1	_			
Turn-On Delay Time	t _{D(ON)}	_	11.3	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 30A, R_{g} = 3\Omega$	
Turn-On Rise Time	t _R	_	28.5	_			
Turn-Off Delay Time	t _D (OFF)	_	86.2	_	ns		
Turn-Off Fall Time	tF	_	47.6	_			
Body Diode Reverse Recovery Time	t _{RR}	_	70.4	_	ns	I- 200 di/dt 4000/	
Body Diode Reverse Recovery Charge	Q_{RR}	_	127	_	nC	$I_F = 30A$, di/dt = 100A/ μ s	

Notes: 5. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

 ^{5.} Device involved on the dark part of the exposed drain pady.
 6. Thermal resistance from junction to soldering point (on the exposed drain pady.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.



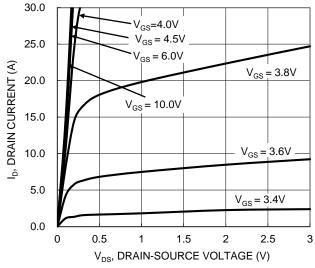


Figure 1. Typical Output Characteristic

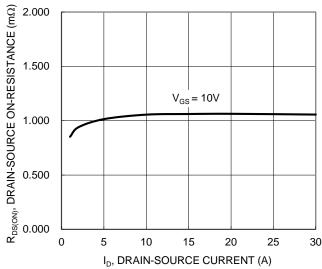


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

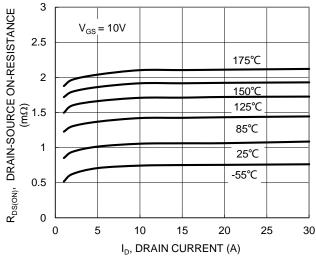


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

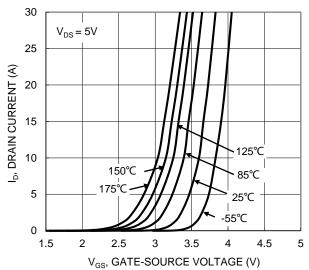


Figure 2. Typical Transfer Characteristic

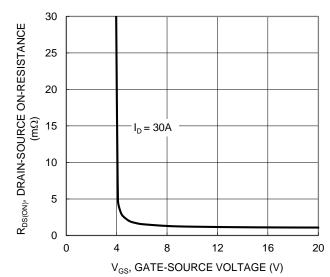


Figure 4. Typical Transfer Characteristic

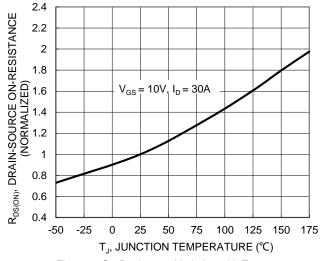


Figure 6. On-Resistance Variation with Temperature



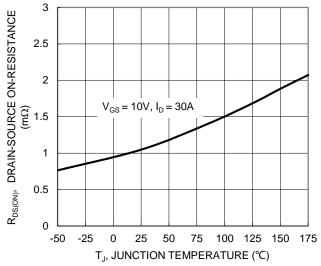


Figure 7. On-Resistance Variation with Temperature

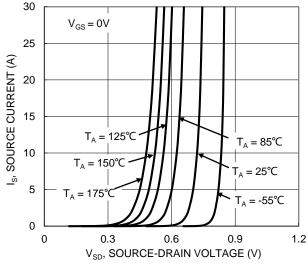


Figure 9. Diode Forward Voltage vs. Current

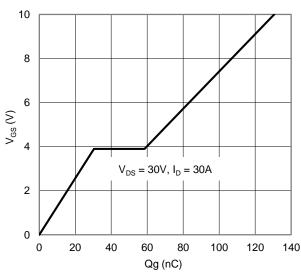


Figure 11. Gate Charge

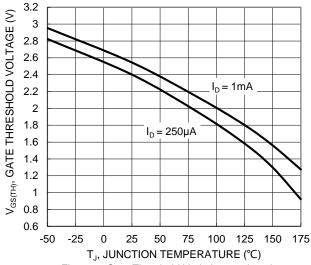
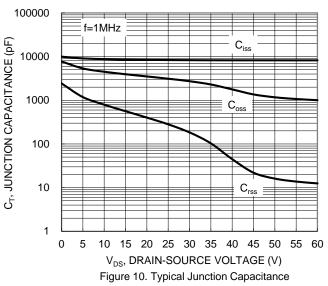


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 $R_{DS(ON)}$ Limited 100 DRAIN CURRENT (A) =10μs P_W =100μs 10 _W =10ms $T_{J(Max)} = 175^{\circ}C$ $T_C = 25^{\circ}C$ P_W =100ms 1 Single Pulse DUT on Infinite Heatsink V_{GS}= 10V 0.1 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



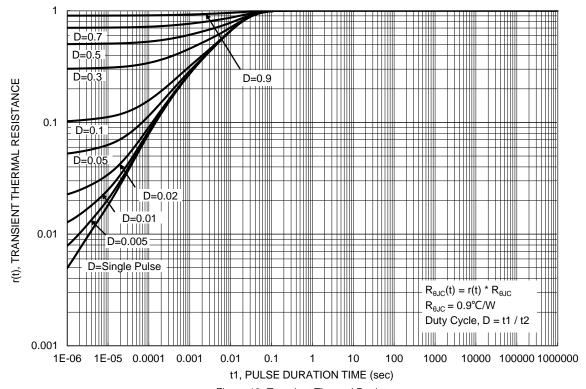


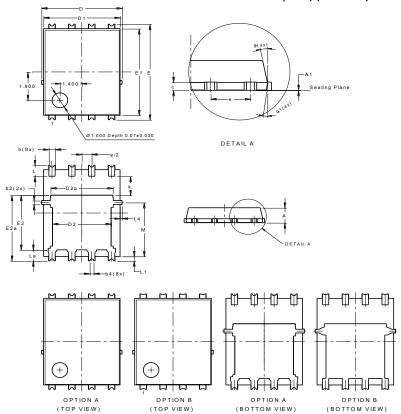
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Standard)

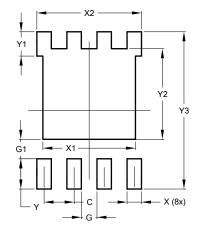


PowerDI5060-8 (SWP) (Standard)			
Dim	Min	Max	Тур
Α	0.90	1.10	1.00
A1	0	0.05	
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	().25REF	•
С	0.230	0.330	0.277
D	5	.15 BS0)
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
Е	6	.40 BS0)
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
е		.27BSC)
k	1.05		
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L4	0.025	0.225	0.125
М	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Standard)



Dimensions	Value		
Difficusions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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